



DC-1.5GHz, 20W, 50V LDMOS Fully matched PA Module

Description

The IMGV0015-20 is a 20-watt, single stage integrated Power Amplifier Module, designed for broad band applications, with frequencies from DC to 1.5GHz. The module is 50 Ω input/output matched and requires minimal external components. **It is recommended for pulsed amplifier ONLY when used at 50V.**

The module implements distributed power amplifier in form of multi chips, housed in cost effective plastic open cavity package, offers a much lower cost than traditional MMIC solutions.



Vds=50V, Idq=150mA, Pulsed CW 10us, 10%

Parameter	100MHz	500MHz	800MHz	1200MHz	1500MHz	1700MHz	Units
Linear Gain	18.0	18.5	18.0	16.2	19.0	17.9	dB
Gain@Pin=30dBm	14.5	14.8	14.1	12.8	14.5	13.5	dB
Pout@Pin=30dBm	28.4	29.8	25.5	20.0	28.0	22.3	W
Eff@Pin=30dBm	74	50	35	27	44	43	%

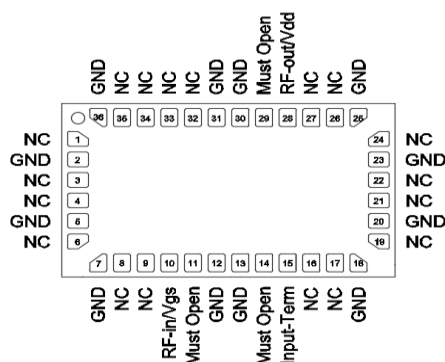
Product Features

- Operating Frequency Range: DC-1.5GHz
- Operating Drain Voltage: +50 V
- 50 Ω Input/Output
- Psat: $\geq 20W$ (Pulse)
- Small signal gain:>16dB, Power gain:>12dB @50V
- Minimum efficiency:>25% @50V
- 6x10 mm Surface Mount Package
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC
- Much lower cost than GaN-based ultrawide band PA , due to LDMOS technology used

Applications

- Ultra Broadband Amplifiers
- Driver for ISM, FM
- Test Instrumentation
- EMC Amplifier Drivers
- HF/VHF 2-way Radios

Pin Configuration and Description





Top View

Pin No.	Symbol	Description
28	RFout/Vdd	Transistor 1, Drain Bias & RF Output
10	RFin/Vgs	Transistor 1, RF Input & Gate Bias
15	Input-Term	Transistor 1, Input 50 ohm term
Others	NC	No connection
11, 14, 29	Must Open	Keep the pin open, no GND
2,5,7,12,13,16,20,23,25, 30, 31,36 Package Base	GND	DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DS}	115	Vdc
Gate--Source Voltage	V_{GS}	-10 to +10	Vdc
Operating Voltage	V_{DD}	+50	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_c	+150	°C
Operating Junction Temperature	T_J	+200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_c = 25^\circ\text{C}$, Pulsed CW Pout=20W@0.5GHz	$R_{\theta JC}$	1.5	°C/W

Table 3. Electrical Characteristics

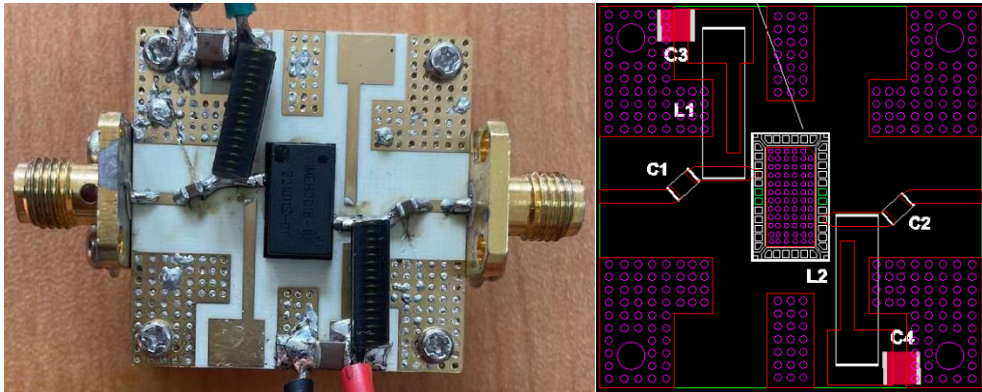
Parameter	Condition	Min	Typ	Max	Unit
Frequency Range	Pin=30dBm	1		1500	MHz
Power Gain @ Psat	Pin=30dBm	12			dB
P_{SAT}	Pin=30dBm	43			dBm
Drain Efficiency @ P_{SAT}	Pin=30dBm	25			%

Unless otherwise noted: $T_A = 25^\circ\text{C}$, $V_{DD} = 50\text{ V}$, Pulse Width=100 us, Duty cycle=10%Load Mismatch of per Section (On Test Fixture, 50 ohm system): $V_{DD} = 50\text{ V}$, $I_{DQ} = 150\text{ mA}$, $f = 0.5\text{ GHz}$

VSWR 10:1 at Psat pulse CW Output Power	No Device Degradation
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Reference Circuit of Test Fixture Assembly Diagram



		Part NO.	Vendor
C3,C4	10uF 100V Chip Capacitor	C5750X7S2A106M230KB	TDK
C1,C2	50V 1uF Chip Capacitor	GRM21BR71H105KA12L	muRata
L1,L2	1.3uH 4.2A Inductor	4310LC-132KEC	Coilcraft
PCB	RO4350B,20mil,er=3.48		

TYPICAL CHARACTERISTICS

Figure 1. Network analyzer output S11/S21 (Pin=0dBm) @50V

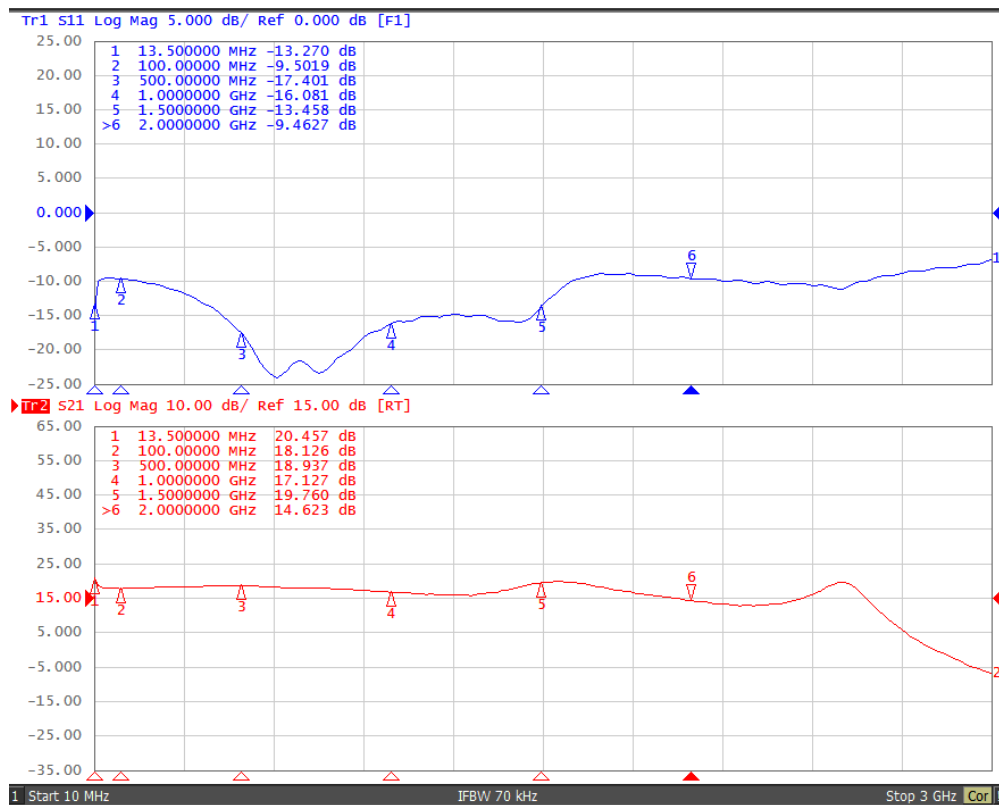
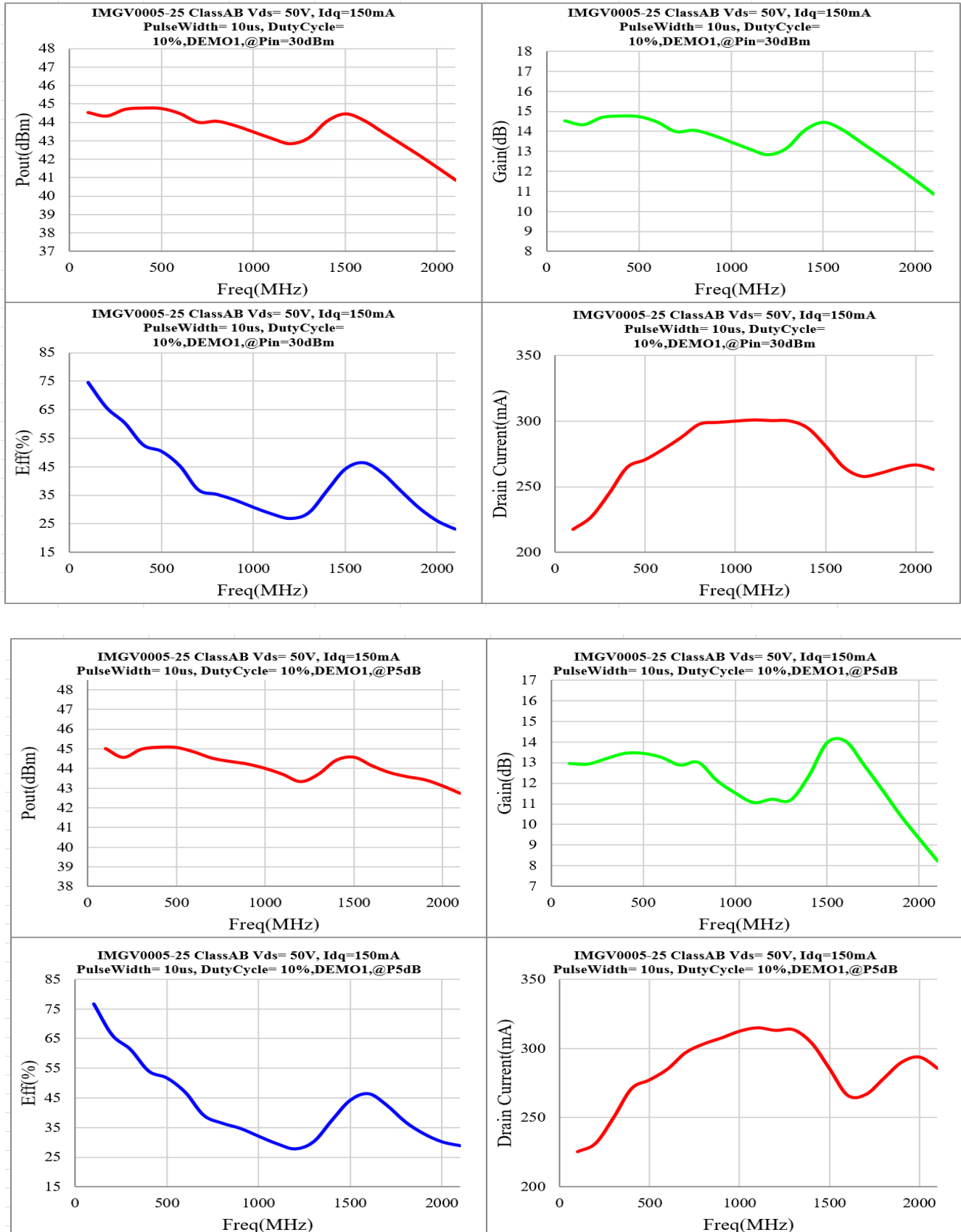


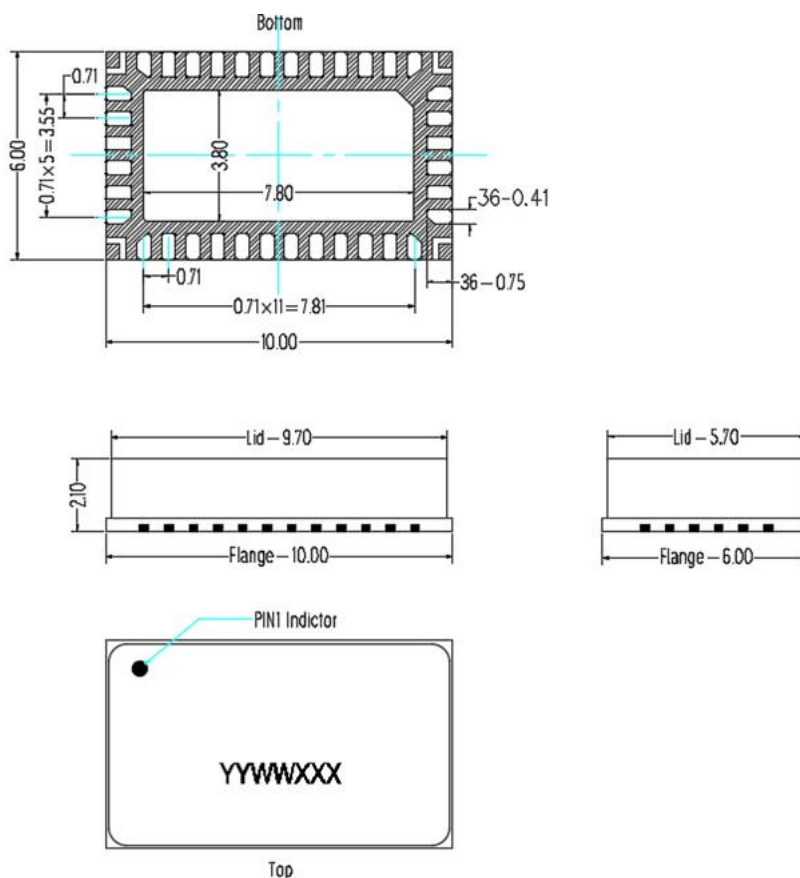


Figure. Power Gain and, efficiency and Pout @Pin=30dBm ,and P5dB vs. Frequency @50V



Package Dimensions

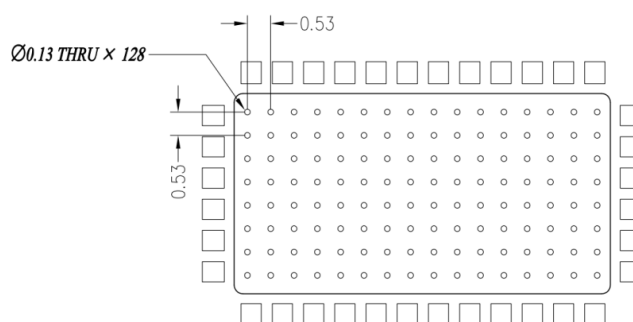
10*6 Plastic Package



Notes:

1. All dimensions are in mm;
2. The tolerances unless specified are $\pm 0.2\text{mm}$.

Mounting Footprint Pattern



Notes:

1. All dimensions are in mm;
2. Vias are required under the backside paddle of this device for proper RF/DC grounding and thermal dissipation. ALL vias are PTH to ground.



Revision history

Table 6. Document revision history

Date	Revision	Datasheet Status
2023/5/13	Rev 1.0	Production Datasheet
2025/9/9	Rev 1.1	Remove 28V data for product planning purpose

Application data based on ZHH-23-07/08

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